Phenomena	Phenomenon monitoring	Cause monitoring	Mitigation	Ground testing	Instruments
		· ·			
		electron spectrum 100eV to 50keV, cold plasma			charged particle
		density (0-100eV), Ion spectrum 100eV to		charging experiments and numerical	detectors(e.g. electrostatic analysers,
		50keV,UV spectrum,	particle emitters, plasma	simulation, secondary	solid state), potential
Spacecraft reference potential change (e.g. so-called spacecraft high voltage		photoemission current, modification of material	contactor, material properties, grounding	yield data, photoemission yield,	probe (e.g. vibrating probe), plasma sensor,
charging).	spacecraft potential	properties in space	strategy	conductivity,	EUV spectrometer
		electron spectrum 100eV			
		to 50keV, cold plasma density (0-100eV), Ion		charging experiments	charged particle detectors(e.g.
		spectrum 100eV to		and numerical	electrostatic analysers,
		50keV,UV spectrum, photoemission current,	particle emitters, plasma contactor, material	yield data,	solid state), potential probe (e.g. vibrating
Differential auriors showing	differential potential	modification of material properties in space	properties, grounding	photoemission yield, conductivity,	probe), plasma sensor, EUV spectrometer
Differential surface charging.	dinerential potential	properties in space	strategy	conductivity,	
			high temperature, material property,	charging experiments and numerical	potential sensor, dose monitor (e.g., solid
			surface coatings,	simulation, secondary	state detector, pin
	internal surface	internal charging currents, electron spectrum	surface grounding, shielding strategy, UV	yield data, photoemission yield,	diode, radFET, photodiode), current
Internal surface charging.	potentials	>40keV, dose-rate	lamp	conductivity,	collection plates.
					potential sensor, dose
					monitor (e.g., solid state detector, pin
					diode, radFET,
	intenal electric fields		high temperature,		photodiode), current collection plates.
	electrical potential embedded charge	internal charging currents, electron spectrum	material property, shielding strategy,		Pulsed Electro Acoustic (PEA) sensor
Deep-dielectric charging	distribution	>40keV, dose-rate	grounding		Acoustic (1 EA) serisor
Surface charging effects on e.g. plasma	electric fields around	plasma density and	electron gun, plasma		langmuir probes?,
instruments.	s/c, sheath thickness	temperature	contactor, bias voltage		plasma instruments QCM
	plume density, plume				Ion spectrometer (0-
Charging interactions with electric thruster plumes.	electric fields, density o charge exchange ions		neutraliser	charge exchange coefficients	100 eV) potential sensor
Charging induced sputtering	sputter rates	ion density, ion momentum	electron gun, plasma contactor	sputter yields v energy	ion spectrometer
				charging experiments and numerical	QCM
				simulation, secondary yield data,	Witness plate (through reflectance
Charging induced molecule and ion			heating	photoemission yield,	measurement)
contamination	contamination rates	contaminant density	ion bombardment	conductivity,	Ion spectrometer
				charging experiments	
		electron spectrum 100eV	potential control	and numerical simulation, secondary	
	dust potential, dust	to 50keV, cold plasma density, Ion spectrum	mechanical covering charging and collecting	yield data, photoemission yield,	ОСМ
Dust charging and sticking	deposition rate	100eV to 50keV, EUV	techniques	conductivity,	optical techniques
		electron spectrum 100eV			
		to 50keV, cold plasma density (0-100eV), Ion			
		spectrum 100eV to			electrostatic analyser,
		50keV,UV spectrum, photoemission current,	particle emitters, plasma contactor, material		potential probe (e.g., Langmuir, vibrating
Electrostatic sticking (SA, inflatables, solar	surface potentials, electrostatic force	modification of material	properties, grounding	charging testing	probe), UV
sails)	electrostatic force	properties in space	strategy	charging testing	spectrometer
		electron spectrum 100eV to 50keV, cold plasma			
		density (0-100eV), Ion	and the continue of the con-	charging experiments	alasta della analasa
		spectrum 100eV to 50keV,UV spectrum,	particle emitters, plasma contactor, material	simulation, secondary	electrostatic analyser, potential probe (e.g.,
Charging differences in docking		photoemission current, modification of material	properties, grounding strategy (e.g. high	yield data, photoemission yield,	Langmuir, vibrating probe), UV
procedures and EVA	frame potential	properties in space	resistance contact)	conductivity,	spectrometer
	material characteristics				
Material modifications (electric field	e.g. conductivity, surface conductivity,	electric field			potential sensor, electric field sensor, ion
induced conductivity, plasma-contaminant	optical properties,	measurement, potential	heating, material		mass spectrometer,
modifications, cracking e.g. of ITO)	cotamination rate	measurement	selection		atomic oxygen sensors potential sensor,
Tether systems and vxB induced voltages	Collected current, particle transport, wave	B field, plasma density, plasma temperature,	current limiting resistance, particle		charged particle energy spectrometer, current
and currents	spectrum	distribution function	emitters, current control		probe
					electrostatic analyser,
Interference induced by electrostatic sheath and induced plasma on EM systems	electromagnetic field in kHz-GHz range	sheath and plasma distribution		plasma experiments	plasma probe (e.g., Langmuir)
	EM field in MHz-GHz range				
	current in MHz-GHz				
	range, location(e.g.		EMC protection,	charging experiments and numerical	
	electrokinetic sensor),	Detected	particle emitters, plasma	simulation, secondary	
Spontaneous discharges and triggered		Potential E-field	contactor, material properties, grounding	yield data, photoemission yield,	antenna current probe, potential
discharges Power loss and current flow from exposed	development	external cause	strategy, geometry	conductivity,	sensor, camera
elevated voltage systems	current budget	coupling to the plasma	control coupling	plasma chamber	current probe
		EUV, X			
		0-100 eV electrons, electron spectrum 100eV	geometry design		particle spectrometer
Photoelectron ans secondary disturbance of		to 50keV, Ion spectrum	choice of material	photo-e and secondary	electrostatic probe,
sensors.	0-100 V potential	100eV to 50keV	potential control	-e characterisation	EUV and X ray sensors radio antenna, high
	o roo v potomia				
Plasma perturbation from microparticle impacts		micro-narticle env	wave filtering	impact test	frequency potential
Plasma perturbation from microparticle impacts (antennas,).	wave form in MHz range	micro-particle env	wave filtering	impact test	
	wave form in MHz range flow speed	micro-particle env	wave filtering	impact test	frequency potential
	wave form in MHz range	micro-particle env	wave filtering	impact test	frequency potential